

November 2014

# SS8050 NPN Epitaxial Silicon Transistor

### **Features**

- 2 W Output Amplifier of Portable Radios in Class B Push-pull Operation.
- · Complimentary to SS8550
- Collector Current: I<sub>C</sub> = 1.5 A



# **Ordering Information**

Part Number	Top Mark	Package	Packing Method
SS8050BBU	S8050	TO-92 3L	Bulk
SS8050CBU	S8050	TO-92 3L	Bulk
SS8050CTA	S8050	TO-92 3L	Ammo
SS8050DBU	S8050	TO-92 3L	Bulk
SS8050DTA	S8050	TO-92 3L	Ammo

# **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at  $T_A = 25^{\circ}\text{C}$  unless otherwise noted.

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	40	V
V <sub>CEO</sub>	Collector-Emitter Voltage	25	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
I <sub>C</sub>	Collector Current	1.5	Α
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-65 to 150	°C

## Thermal Characteristics(1)

Values are at  $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter	Value	Unit
D	Power Dissipation	1	W
P <sub>D</sub>	Derate Above 25°C	8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	125	°C/W

### Note:

1. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

## **Electrical Characteristics**

Values are at  $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 100 \mu\text{A}, I_E = 0$	40			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_C = 2 \text{ mA}, I_B = 0$	25			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 100  \mu A, I_C = 0$	6			V
I <sub>CBO</sub>	Collector Cut-Off Current	$V_{CB} = 35 \text{ V}, I_{E} = 0$			100	nA
I <sub>EBO</sub>	Emitter Cut-Off Current	$V_{EB} = 6 \text{ V}, I_{C} = 0$			100	nA
h <sub>FE1</sub>		$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}$	45			
h <sub>FE2</sub>	DC Current Gain	$V_{CE} = 1 \text{ V, } I_{C} = 100 \text{ mA}$	85		300	
h <sub>FE3</sub>		$V_{CE} = 1 \text{ V, } I_{C} = 800 \text{ mA}$	40			
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	$I_C = 800 \text{ mA}, I_B = 80 \text{ mA}$			0.5	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	$I_C = 800 \text{ mA}, I_B = 80 \text{ mA}$			1.2	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	$V_{CE} = 1 \text{ V, } I_{C} = 10 \text{ mA}$			1	V
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1 MHz		9.0		pF
f <sub>T</sub>	Current Gain Bandwidth Product	$V_{CE} = 10 \text{ V}, I_{C} = 50 \text{ mA}$	100			MHz

# h<sub>FE</sub> Classification

Classification	В	С	D
h <sub>FE2</sub>	85 ~ 160	120 ~ 200	160 ~ 300

# **Typical Performance Characteristics**

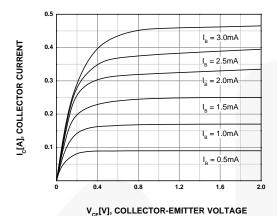


Figure 1. Static Characteristic

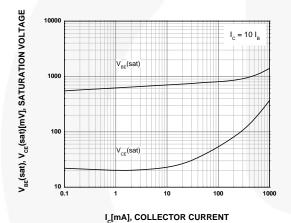


Figure 3. Base-Emitter Saturation Voltage and Collector-Emitter Saturation Voltage

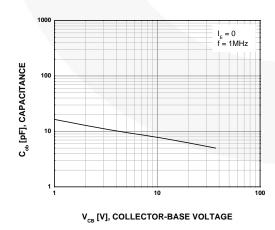


Figure 5. Collector Output Capacitance

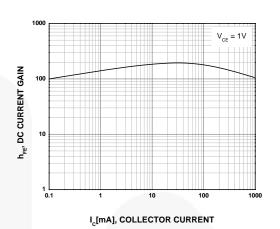


Figure 2. DC Current Gain

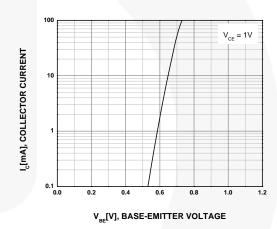


Figure 4. Base-Emitter On Voltage

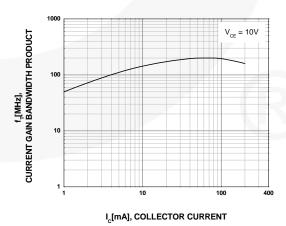
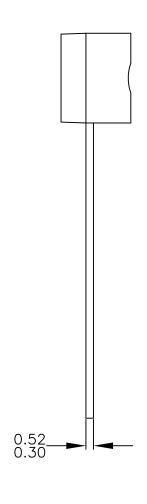


Figure 6. Current Gain Bandwidth Product

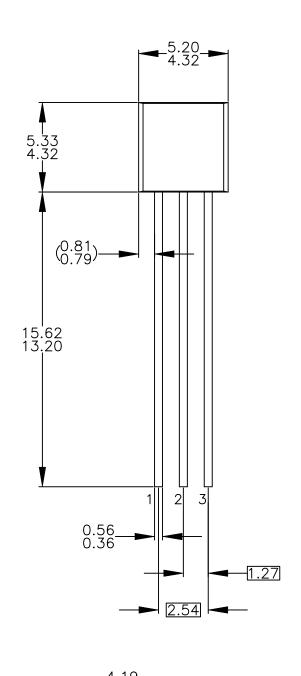






### NOTES: UNLESS OTHERWISE SPECIFIED

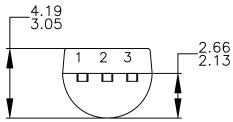
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NOTES: UNLESS OTHERWISE SPECIFIED

- DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS.
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  DRAWING FILENAME: MKT-ZAO3DREV4.









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Definition of Terms				
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